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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

K. Takahashi, et al.

Atty. Dkt. 03680036AA

Serial No. Not assigned

Group Art Unit: not assigned

Filed: concurrently

Examiner: not assigned

For: Semiconductor Device and Method of Fabricating the same

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Under the provisions of 37 C.F.R. 1.97 through 1.98 and pursuant to applicants' duty of disclosure under 37 C.F.R. 1.56, applicants respectfully bring the following documents, as listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. Copy of the listed document is provided herewith for the convenience of the Examiner.

It is respectfully requested that the listed references be considered by the Examiner and formally made of record in this application.

If any fees are due with the filing of this Information Disclosure Statement, please charge Deposit Account No. 50-2041.

Respectfully submitted,

Date: April 14, 2006

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ATTY DOCKET NO. 03680036AA INFORMATION DISCLOSURE CITATION K. Takahashi, et al. (Use several sheets if necessary) FILING **GROUP ART** concurrently not assigned **U.S. PATENT DOCUMENTS** *EXAMINER FILING DATE DOCUMENT NUMBER DATE NAME CLASS SUBCLASS INITIAL IF APPROPRIATE **U.S. PATENT APPLICATION PUBLICATIONS** *EXAMINER FILING DATE DOCUMENT NUMBER DATE NAME CLASS SUBCLASS INITIAL IF APPROPRIATE **FOREIGN PATENT DOCUMENTS** TRANSLATION DOCUMENT NUMBER DATE COUNTRY CLASS SUBCLASS YES NO OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Kedzierski, J., et al., "Threshold voltage control in NiSi-gated MOSFETs through silicidation induced impurity segregation (SIIS)", IEEE (2003) CC Maszara, W.P., et al., "Transistors with Dual Work Function Gates by Single Full Silicidation (FUSI) of Polysilicon Gates", IEEE (2002) CD **EXAMINER DATE CONSIDERED** *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not

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considered. Include copy of this form with next communication to applicant.

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